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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Application Number	09/945512
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2812
Examiner Name	Richard A. Booth

Sheet 1 of 2

Attorney Docket No: 01303.027US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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	US-4780424	10/25/1988	Holler, M. A.	437	29	09/28/1987
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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
RAB		ARYA, S., et al, "Conduction Properties of Thin Al ₂ O ₃ Films", <u>Thin Solid Films</u> , 91, (1982), pp. 363-374	
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		ELDRIDGE, J.M. et al, "Measurement of Tunnel Current Density in a Metal-Oxide-Metal System as a Function of Oxide Thickness", <u>Proc. 12th Intern. Conf. on Low Temperature Physics</u> , (1971), pp. 427-428	
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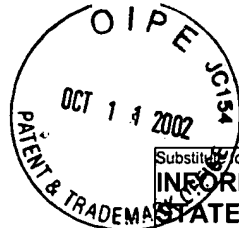
Richard A. Booth

DATE CONSIDERED

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AB		Junctions Produced by Plasma and by Thermal Oxidation", <u>Surface Science</u> , 27, (1971), pp. 125-141	
		HODGES, D.A. et al, <u>Analysis and Design of Digital Integrated Circuits</u> , McGraw-Hill Book Company, 2nd Edition, (1988), pp. 394-396	
		HURYCH, Z., "Influence of Non-Uniform Thickness of Dielectric Layers on Capacitance and Tunnel Currents", <u>Solid-State Electronics</u> , Vol. 9, (1966), pp. 967-979	
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